



Attorney Docket No.: LOVO-033.CON

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
Patent Application

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Group Art Unit: 2816

Filed: 06/26/03

Examiner:

Application No.: 10/609,253

Title: STARTER DEVICE FOR NORMALLY OFF JFETS

Form 1449**U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A						

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	B							

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
ATL	C	H. Ogiwara, M. Hayakawa, T. Nishimura and M. Nakaoka; "HIGH-FREQUENCY INDUCTION HEATING INVERTER WITH MULTI-RESONANT MODE USING NEWLY DEVELOPED NORMALLY-OFF TYPE STATIC INDUCTION TRANSISTORS"; Department of Electrical Engineering, Ashikaga Institute of Technology, Japan; Department of Electrical Engineering, Oita University, Japan; Department of Electrical Engineering, Kobe University, Japan; pages 1017-1023
AK	D	J. Baliga; "HIGHVOLTAGE JUNCTION-GATE FIELD EFFECT TRANSISTOR WITH RECESSED GATES"; IEEE Transactions on Electron Devices; Vol. ED-29; No. 10; Oct. 1982
AK	E	J. M. C. Stork et al.; "SMALL GEOMETRY DEPLETED BASE BIPOLAR TRANSISTORS (BSIT)- VLSI DEVICES?"; IEEE Transactions on Electron Devices; Vol. ED-28; No. 11; Nov. 1981
AK	F	Nishizawa et al.; "ANALYSIS OF STATIC CHARACTERISTICS OF A BIPOLAR MODE SIT (BSIT)"; IEEE Transactions on Electron Devices; Vol. ED-29; No. 11; Aug. 1982
AK	G	Caruso et al.; "PERFORMANCE ANALYSIS OF A BIPOLAR MODE FET (BMFET) WITH NORMALLY OFF CHARACTERISTICS"; IEEE Transactions on Power Electronics; Vol. 3; No. 2; April 1988
AK	H	Nishizawa et al.; "FIELDEFFECT TRANSISTOR VERSUS ANALOG TRANSISTOR (STATIC INDUCTION TRANSISTOR)"; IEEE Transactions on Electron Devices; Vol. ED-24; No. 4; April 1975
Examiner LLL		Date Considered 11/29/04

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.